

Technical Data

DIODE



maximum ratings

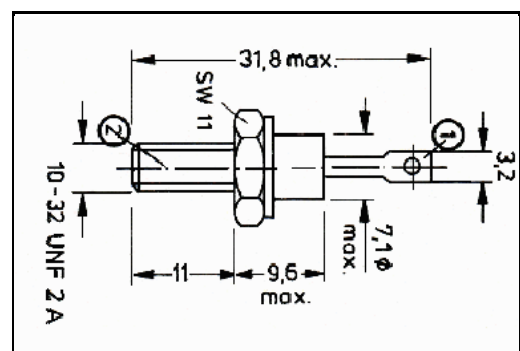
Voltage, Reverse (VR)	1000.0	V	NO.	1N3673A-M
Voltage, Reverse Peak (VRM)	1000.0	V	TYPE	SILICON
Current at VR = 0V (IO)		A		
Current Average Rectified (IF)	12.0	A		
Current Surge Peak (IZM)		A	CASE	DO-4_UNF
Current, Surge (IFM) at tp = 8.3 ms	240.0	A		MIL-S-19500
Max. Power Dissipation (PT) at TC = °C		W		BURN-IN 48h/125°C
Max. Thermal Resistance (Rth J-C)	2.0	°C/W		
Max. Junction Temperature (TJ)	150.0	°C		

PERFORMANCE CHARACTERISTICS at $T_c = 25^\circ\text{C}$, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	IR	VR = 1000.0 V	-	50.0	μA
2.	IR	VR = 1000.0 V, TJ = 125.0° C	-	1.0	mA
3.	VF	IF = 12.0 A (1)	-	1.1	V
4.	trr	IF = 1.0 A, VR = 30.0 V	-	5.0	μs
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Notes (1)pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

DIMENSIONS
in mm



Marking 1N3673A-M + GREEN DOT
Customer GENERAL PURPOSE